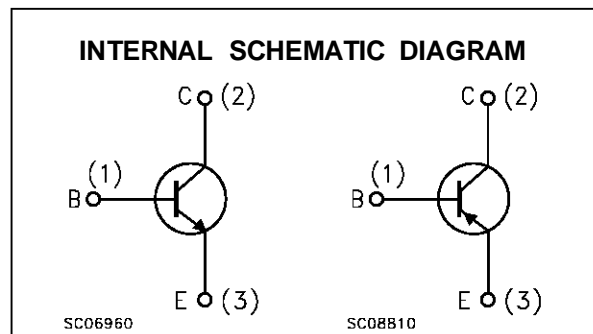
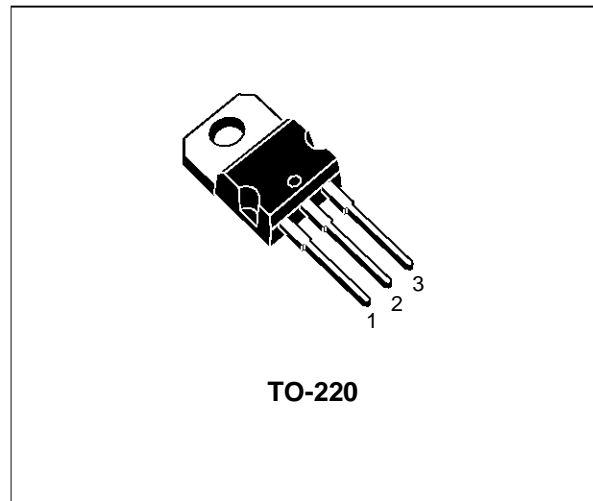


COMPLEMENTARY SILICON POWER TRANSISTORS

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The TIP41A, TIP41B and TIP41C are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intended for use in medium power linear and switching applications. The complementary PNP types are TIP42A, TIP42B and TIP42C.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit	
		NPN	TIP41A	TIP41B		TIP41C
		PNP	TIP42A	TIP42B		TIP42C
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	80	100	V	
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	80	100	V	
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5			V	
I_C	Collector Current	6			A	
I_{CM}	Collector Peak Current	10			A	
I_B	Base Current	3			A	
P_{tot}	Total Dissipation at $T_{case} \leq 25\text{ }^\circ\text{C}$ $T_{amb} \leq 25\text{ }^\circ\text{C}$	65			W	
		2			W	
T_{stg}	Storage Temperature	-65 to 150			$^\circ\text{C}$	
T_j	Max. Operating Junction Temperature	150			$^\circ\text{C}$	

TIP41A/TIP41B/TIP41C/TIP42A/TIP42B/TIP42C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.92	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

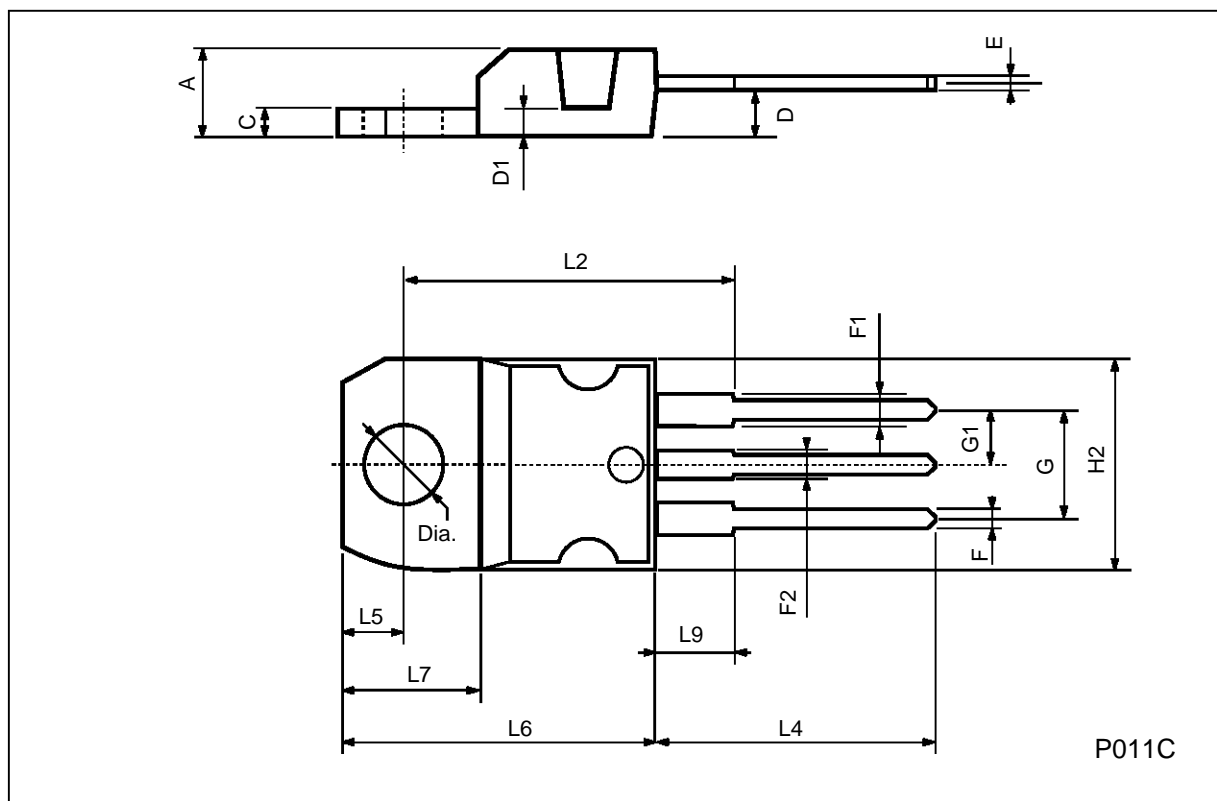
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _B = 0)	for TIP41A/42A V _{CE} = 30 V for TIP41B/41C/42B/42C V _{CB} = 60 V			0.7	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for TIP41A/42A V _{CE} = 60 V for TIP41B/42B V _{CE} = 80 V for TIP41C/42C V _{CE} = 100 V			0.4	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP41A/42A for TIP41B/42B for TIP41C/42C	60 80 100			V V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 6 A I _B = 0.6 A			1.5	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 6 A V _{CE} = 4 V			2	V
h _{FE} *	DC Current Gain	I _C = 0.3 A V _{CE} = 4 V I _C = 3 A V _{CE} = 4 V	30 15		75	
h _{fe}	Small Signal Current Gain	I _C = 0.5 A V _{CE} = 10 V f = 1 KHz I _C = 0.5 A V _{CE} = 10 V f = 1 MHz	20 3			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %
For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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